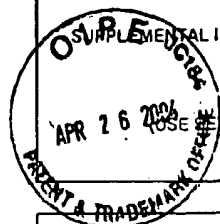


FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
MICRON.129DV1C1APPLICATION NO.  
10/758,518SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

USE SEVERAL SHEETS IF NECESSARY)

APPLICANT  
Ronald A. WeimerFILING DATE  
January 15, 2004GROUP  
Unknown

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DM	5,264,724	11/23/93	Brown et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER  
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)


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EXAMINER

DATE CONSIDERED

7/8/04

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT MAR 29 2004 (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.129DV1C1	APPLICATION NO. 10/758,518
	APPLICANT Ronald A. Weimer	
	FILING DATE January 15, 2004	GROUP Unknown

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DM	1	4,142,004	02/27/79	Hauser, Jr. et al.			
DM	2	4,551,231	11/05/85	Kovach et al.			
DM	3	4,623,912	11/18/86	Chang et al.			
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DM	6	5,102,832	04/07/92	Tuttle			
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DM	27	6,017,784	01/25/00	Ohta et al.			
DM	28	6,017,808	01/25/00	Wang et al.			

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DATE CONSIDERED

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		FILING DATE January 15, 2004	GROUP Unknown

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DM	29	6,025,281	02/15/00	Passlack et al.			
DM	30	6,048,795	04/11/00	Numasawa et al.			
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EXAMINER <i>Rogers</i>	DATE CONSIDERED <i>7/8/04</i>
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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
DM	57	Cheng et al., Effects of NH <sub>3</sub> Plasma Passivation on N-Channel Polycrystalline Silicon Thin-Film Transistors, IEEE, Vol. 44, No. 1, pp. 64-68, January 1997.
DM	58	U.S. Patent Application No. 10/377,495 entitled "AMMONIA GAS PASSIVATION ON NITRIDE ENCAPSULATED DEVICES" in 28 pages with 5 sheets of drawings.
DM	59	U.S. Patent Application No. 10/012,665 entitled "AMMONIA GAS PASSIVATION ON NITRIDE ENCAPSULATED DEVICES" in 21 pages with 5 sheets of drawings.
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